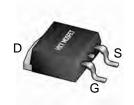


Description

The AUIRFR3504Z uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.



TO-252-2L

General Features

 $V_{DS} = 40V I_{D} = 60A$

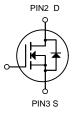
 $R_{DS(ON)}$ < 8.5m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AUIRFR3504Z	TO-252-2L	AUIRFR3504Z XXXX	2500

Absolute Maximum Ratings (T_c=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units	
V _D s	Drain-Source Voltage	40	V	
Vgs	Gate-Source Voltage	e Voltage ±20		
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	60	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	45	А	
Ідм	Pulsed Drain Current ²	220	А	
EAS	Single Pulse Avalanche Energy ³	416.1	mJ	
las	Avalanche Current	39	Α	
P _D @T _C =25°C	Total Power Dissipation ⁴	64.6	W	
Тѕтс	Storage Temperature Range -55 to 150		°C	
TJ	Operating Junction Temperature Range -55 to 150		°C	
ReJA	Thermal Resistance Junction-ambient (Steady State) ¹	62	°C/W	
Rejc	Thermal Resistance Junction-Case ¹	2.8	°C/W	



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40	45	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.2	1.6	2.0	V	
Dunin Course On Otata Basistana	-	V _{GS} =10V, I _D =20A	-	7.0	8.5	0	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A		15	18	mΩ	
Forward Transconductance	g FS	V _{DS} =10V,I _D =20A	15	-	-	S	
Input Capacitance	C _{lss}	\/ 00\/\/ 0\/	-	1800	-	PF	
Output Capacitance	C _{oss}	V_{DS} =20V, V_{GS} =0V,	-	280	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	190	-	PF	
Turn-on Delay Time	t _{d(on)}		-	6.4	-	nS	
Turn-on Rise Time	t _r	V_{DD} =20 V , I_D =2 A , R_L =1 Ω	-	17.2	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	29.6	-	nS	
Turn-Off Fall Time	t _f		-	16.8	-	nS	
Total Gate Charge	Qg	\/ 00\/\ 00A	-	29		nC	
Gate-Source Charge	Q _{gs}	V _{DS} =20V,I _D =20A,	-	4.5		nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	6.4		nC	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =10A	-		1.2	V	
Diode Forward Current (Note 2)	Is		-	-	68	Α	
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	29	-	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	26	-	nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition : $Tj=25\,^{\circ}\text{C}$, $V_{DD}=20\text{V}$, $V_{G}=10\text{V}$,L=1mH, $Rg=25\Omega$,

Typical Electrical and Thermal Characteristics (Curves)

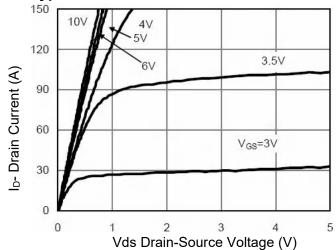


Figure 1 Output Characteristics

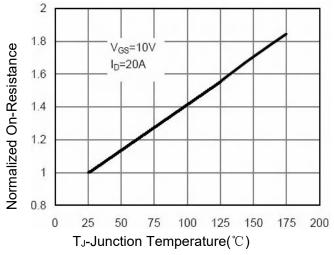


Figure 4 Rdson-JunctionTemperature

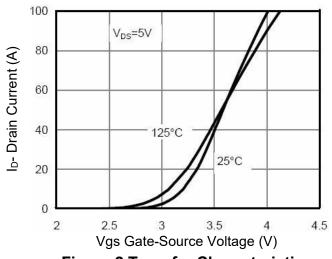


Figure 2 Transfer Characteristics

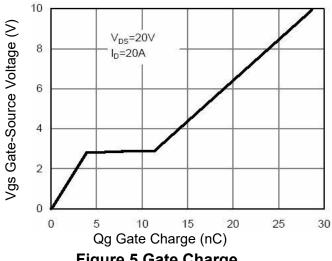


Figure 5 Gate Charge

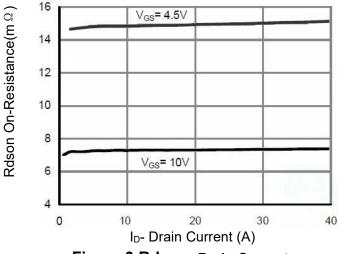


Figure 3 Rdson- Drain Current

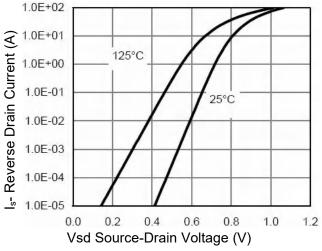
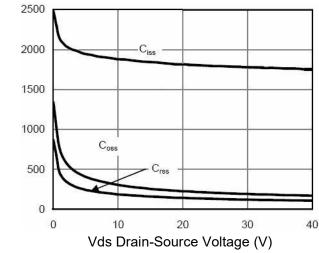
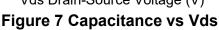
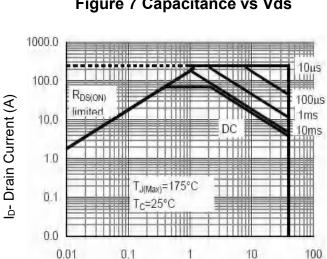


Figure 6 Source- Drain Diode Forward

C Capacitance (pF)







Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area

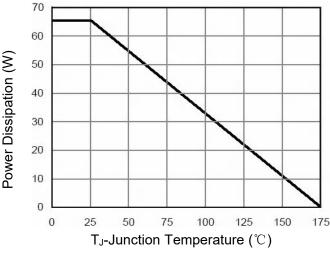


Figure 9 Power De-rating

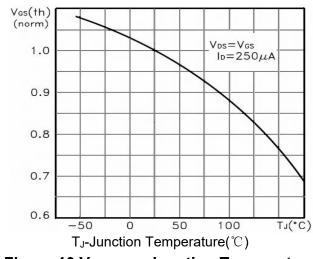


Figure 10 V_{GS(th)} vs Junction Temperature

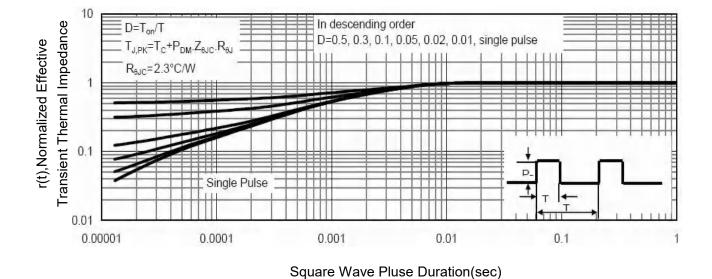
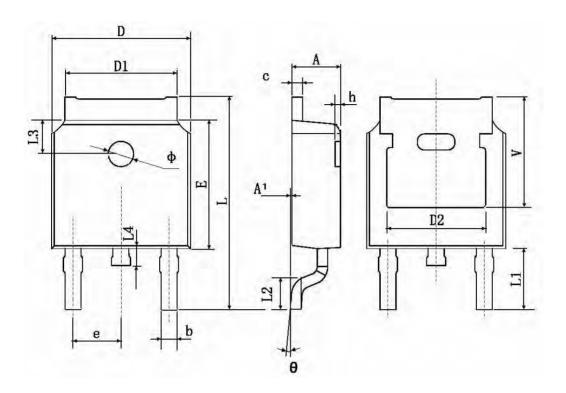


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		



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